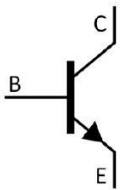


Silicon NPN transistor in a SOT-23 Plastic Package.

High h_{FE} complementary pair with 2SA1981S.

Audio power amplifier applications



PIN1 Base

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HFAO	HFAY



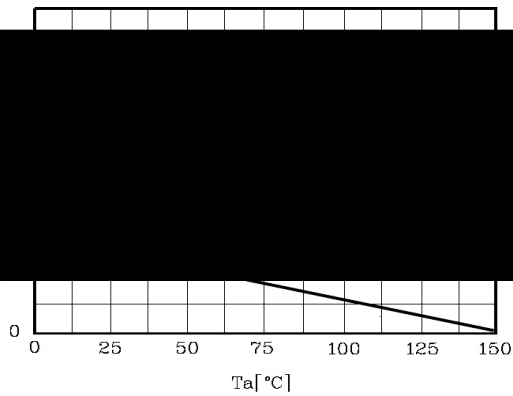
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	35			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=1.0V$ $I_C=100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$			0.5	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $I_C=10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$ $I_E=0$		13		pF

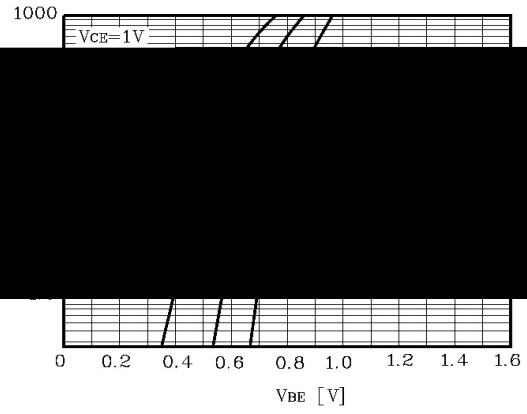




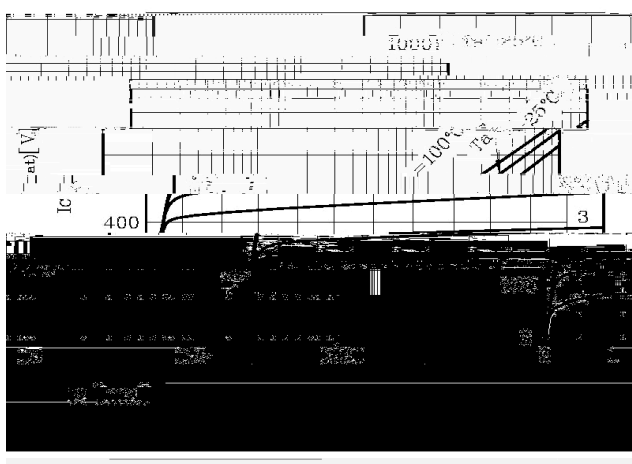
$P_C - T_a$



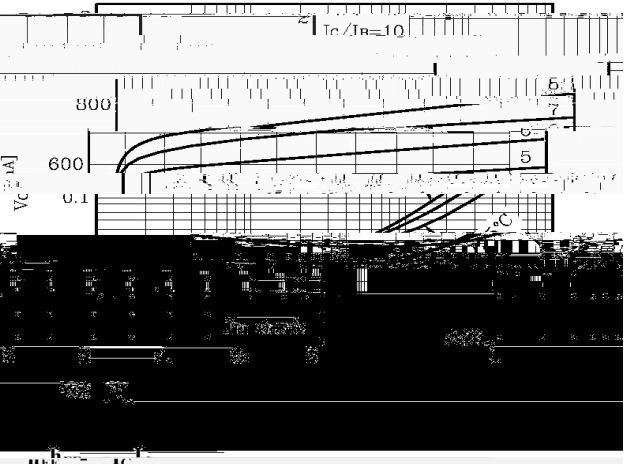
$I_C - V_{BE}$



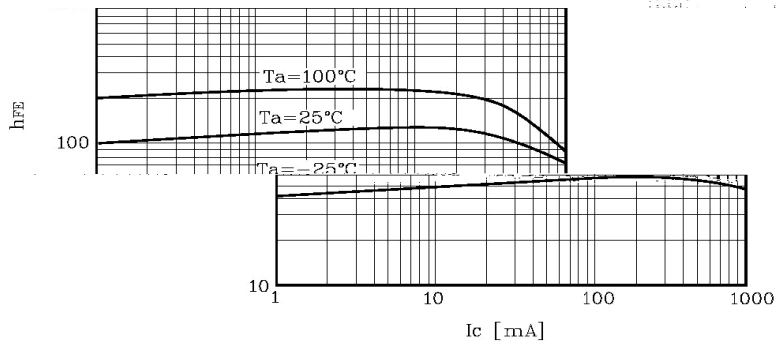
$I_C - V_{CE}$



$V_{CE(sat)} - I_C$



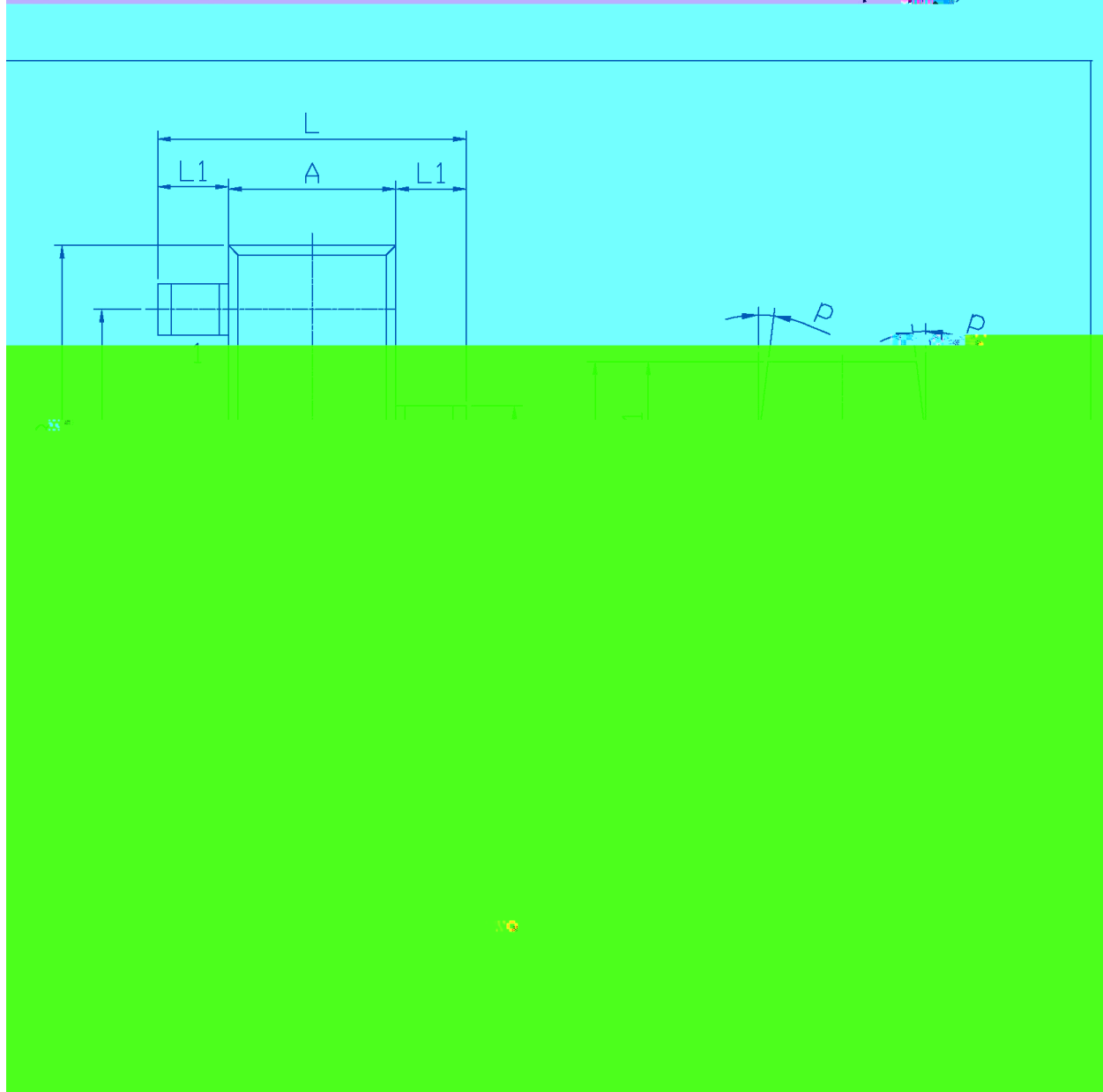
$h_{FE} - I_C$

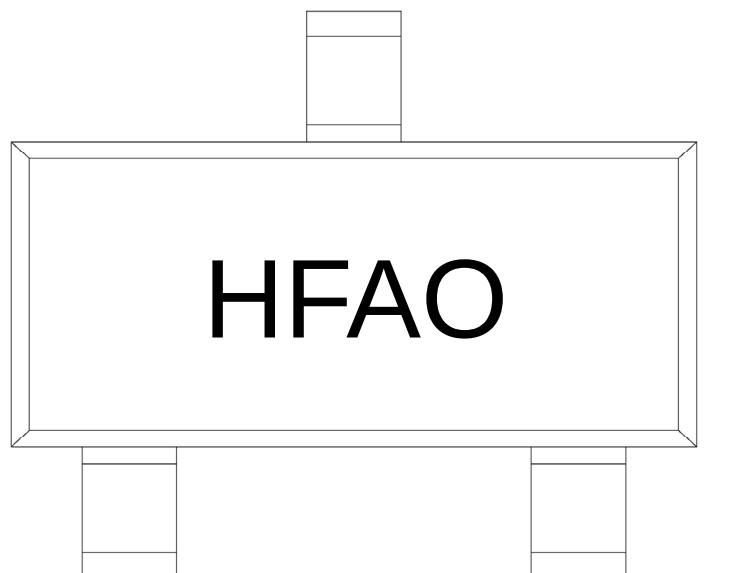




SOT-23

单位: mm



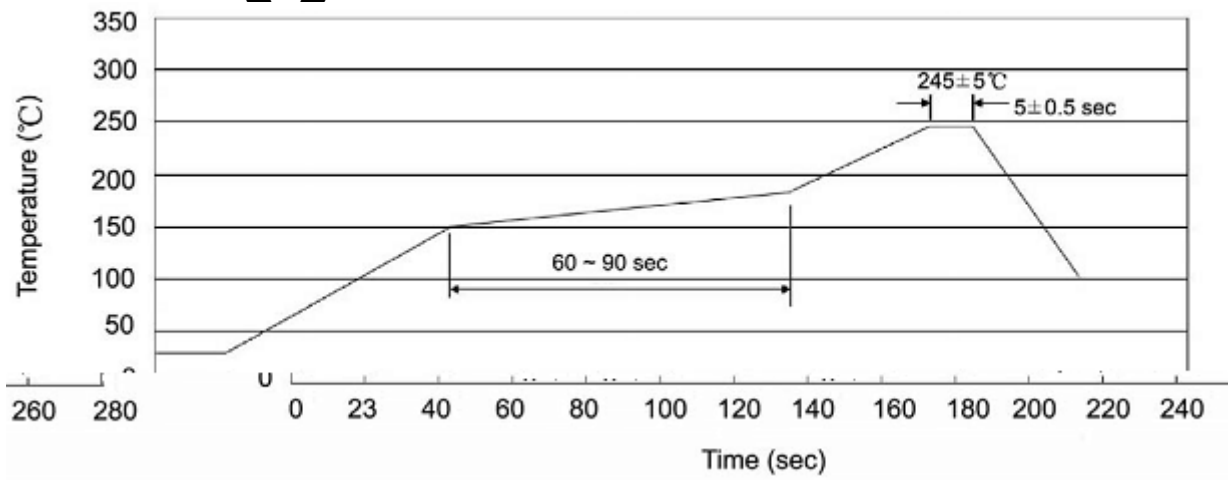


Note:

Company Code

Product Type Code

h_{FE} Classifications Symbol Code



Note:

- 1251506090sec;1.Preheating:25~150,Time:60~90sec.
- 22455245±5,Duration:50.5sec.
- 3/ /sec.

2601sec.

Temp.:260±5°C

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量				Dimension 包装尺寸 (unit: mm ³)		
	盘盒	只盒	盒箱	只箱	盒	箱	
					"		